



ACE12201B

P-Channel Enhancement Mode Power MOSFET

Description

The ACE12201B uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a load switch or battery protection applications.

Features

- $V_{DS} (V) = -20V$
- $I_D = -8.5A$
- $R_{DS(ON)} \leq 28m\Omega @V_{GS} = -4.5V$
- $R_{DS(ON)} \leq 30m\Omega @V_{GS} = -4.0V$
- $R_{DS(ON)} \leq 40m\Omega @V_{GS} = -2.5V$
- $R_{DS(ON)} \leq 61m\Omega @V_{GS} = -1.8V$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 10	V
Drain Current (Continuous) ^{*AC}	I_D	$T_A=25^\circ C$	-8.5
		$T_A=100^\circ C$	-6.3
Drain Current (Pulse) ^{*B}	I_{DM}	-33	A
Power Dissipation	P_D	2.8	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	80	$^\circ C/W$

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$. The value in any given application depends on the user's specific board design.

B. Repetitive rating, pulse width limited by junction temperature.

C. The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.

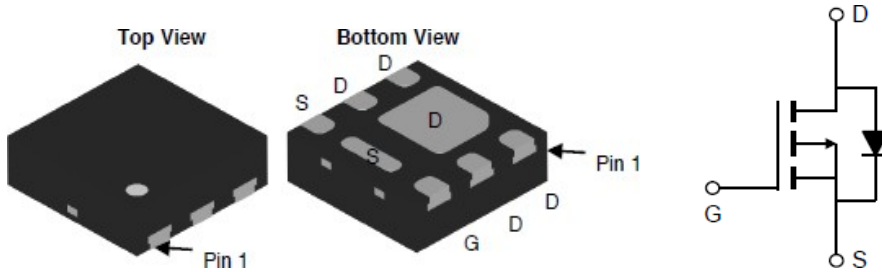


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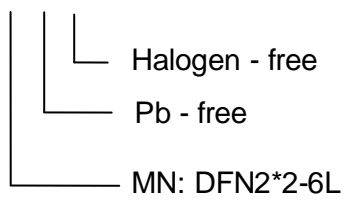
Packaging Type

DFN2*2-6L



Ordering information

ACE12201B XX + H





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Electrical Characteristics $T_A=25\text{ }^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-0.4	-0.55	-1	V
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-5.5A$		22	28	m Ω
		$V_{GS}=-4.0V, I_D=-4.0A$		23	30	
		$V_{GS}=-2.5V, I_D=-4.0A$		28	40	
		$V_{GS}=-1.8V, I_D=-2.5A$		37	61	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-8A$	15			S
Diode Forward Voltage	V_{SD}	$I_{SD}=-1A, V_{GS}=0V$			-1	V
Diode Forward Current	I_S				-4.5	A
Switching						
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-8A$ $V_{GS}=-4.5V$		13		nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			3.4		
Turn-On Delay Time	$T_{d(on)}$	$V_{GS}=-10V, V_{DS}=-4.5V$ $R_L=1.25\Omega, R_{GEN}=3\Omega$		7		ns
Turn-On Rise Time	t_f			28		
Turn-Off Delay Time	$t_{d(off)}$			95		
Turn-Off Fall Time	t_f			46		
Dynamic						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V$ $f=1.0MHz$		1025		pF
Output Capacitance	C_{oss}			167		
Reverse Transfer Capacitance	C_{rss}			119		



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Typical Performance Characteristics

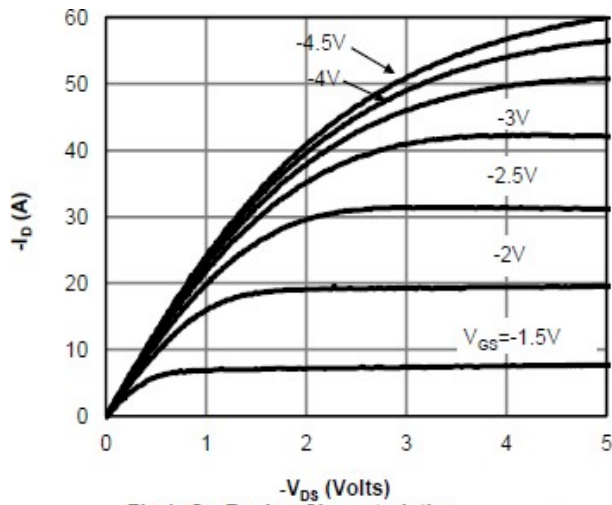


Fig 1: On-Region Characteristics

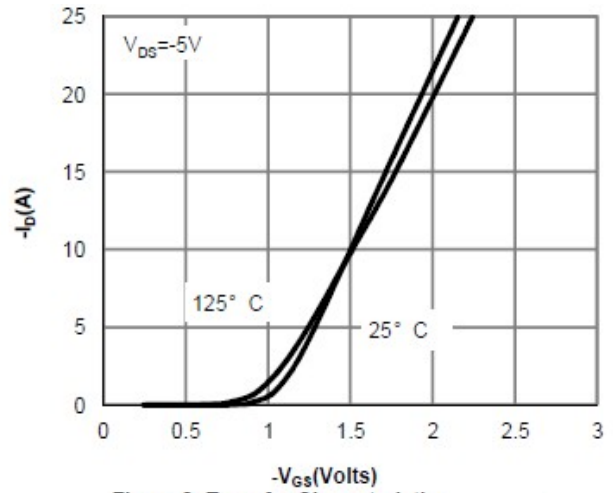


Figure 2: Transfer Characteristics

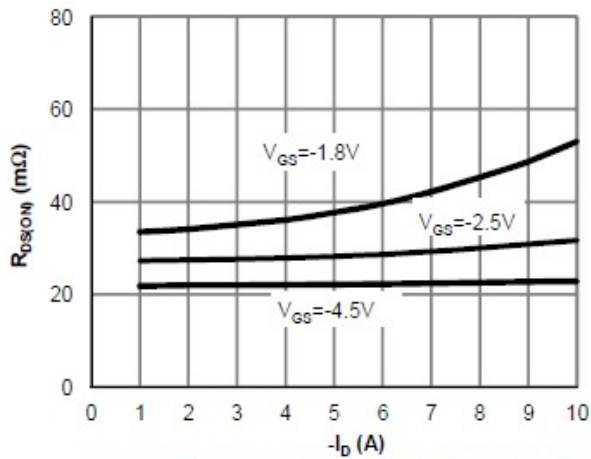


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

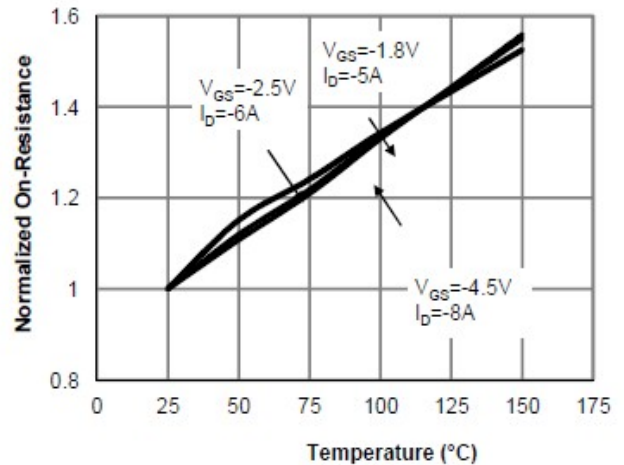


Figure 4: On-Resistance vs. Junction Temperature

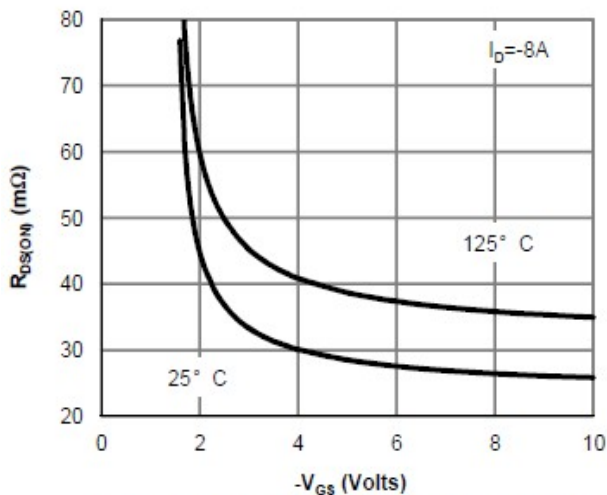


Figure 5: On-Resistance vs. Gate-Source Voltage

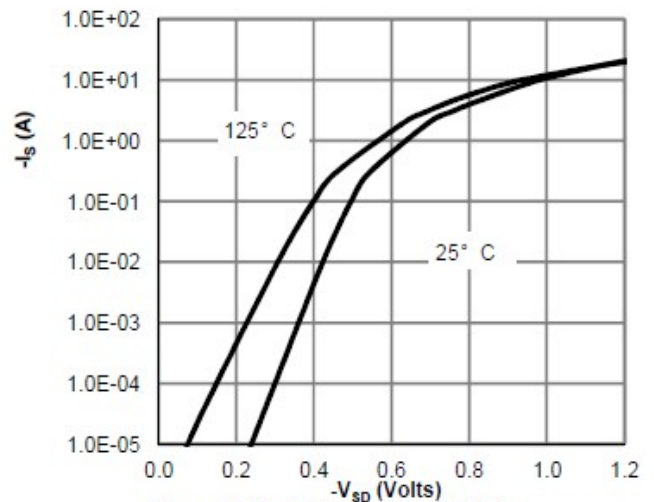


Figure 6: Body-Diode Characteristics



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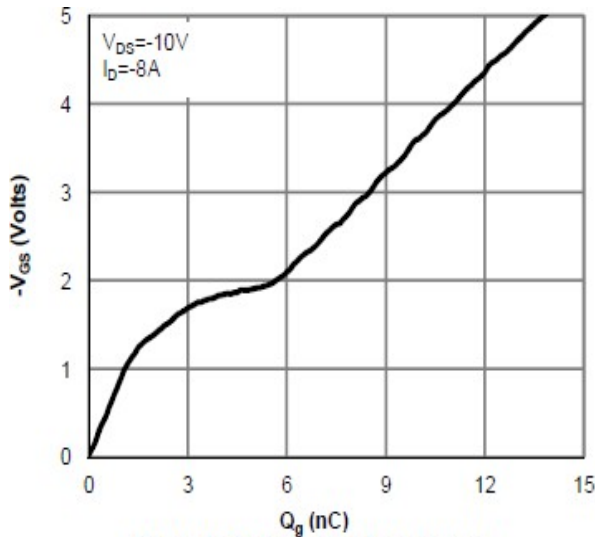


Figure 7: Gate-Charge Characteristics

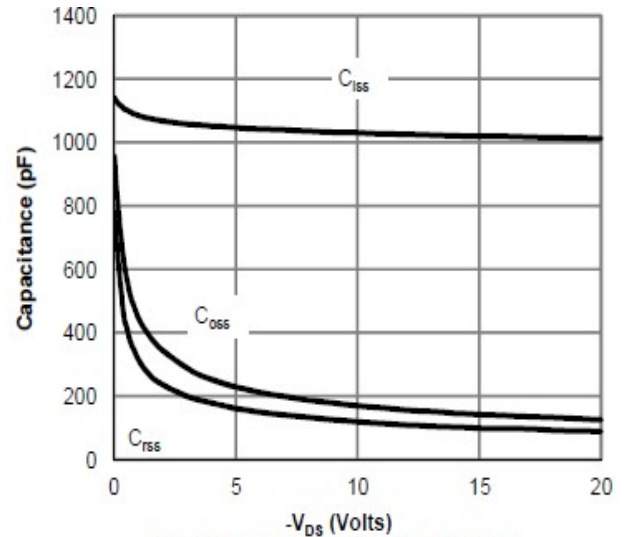


Figure 8: Capacitance Characteristics

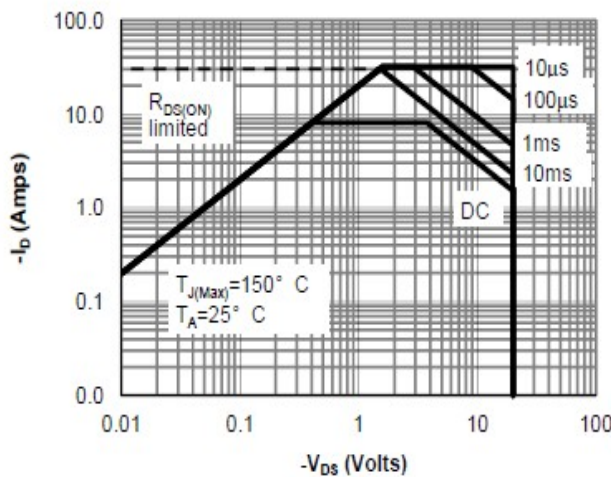


Figure 9: Maximum Forward Biased Safe Operating Area

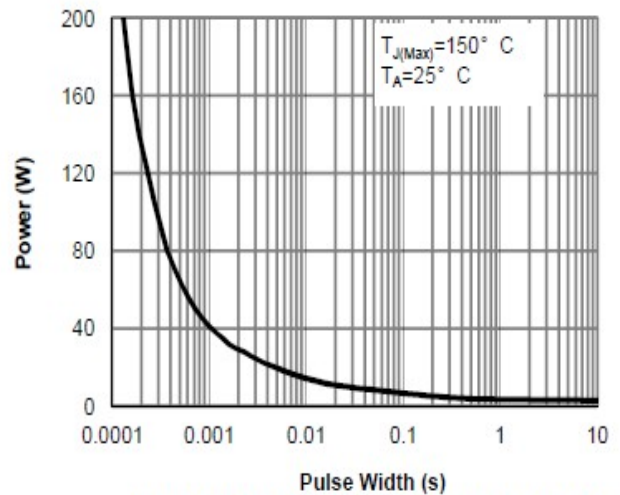


Figure 10: Single Pulse Power Rating Junction-to-Ambient

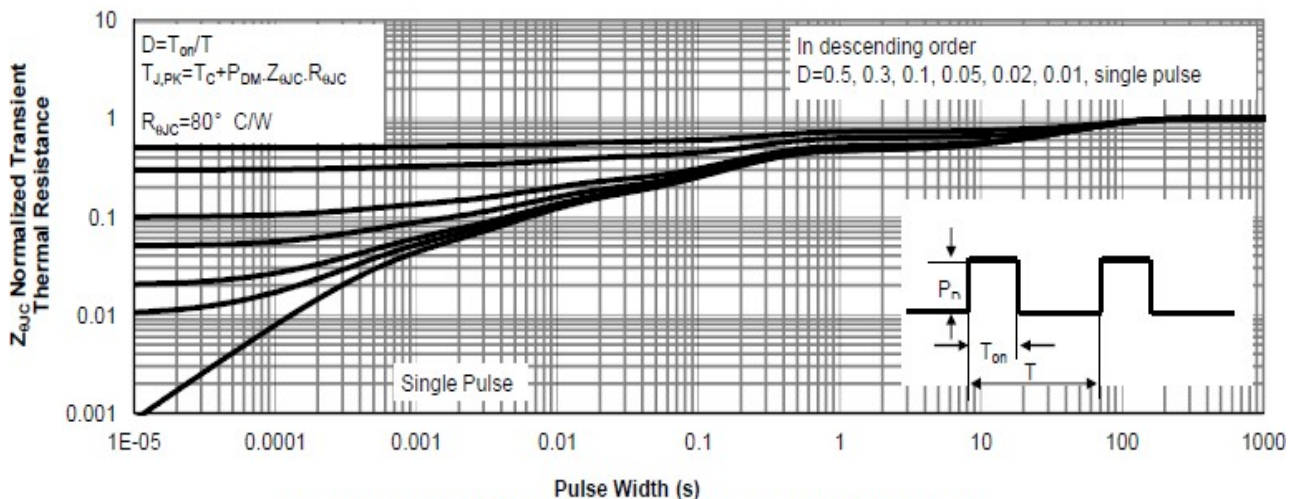


Figure 11: Normalized Maximum Transient Thermal Impedance

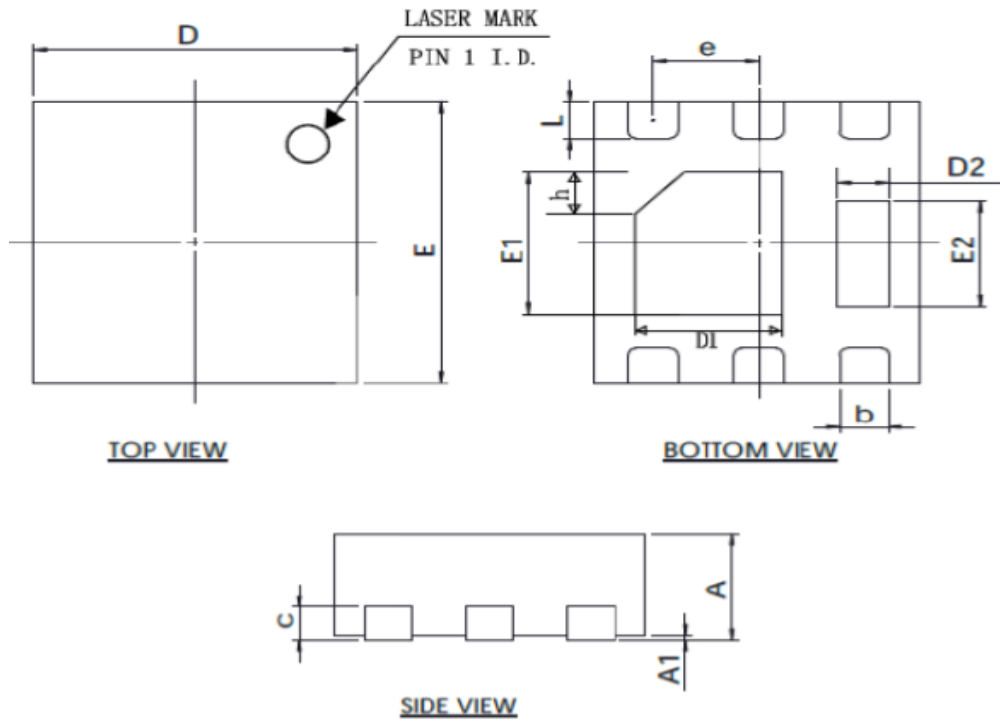


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Packing Information

DFN2*2-6L



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	NA	0.02	0.05
b	0.20	0.27	0.34
c	0.18	0.20	0.25
D	1.95	2.00	2.07
E	1.95	2.00	2.07
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
e	0.65BSC		



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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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